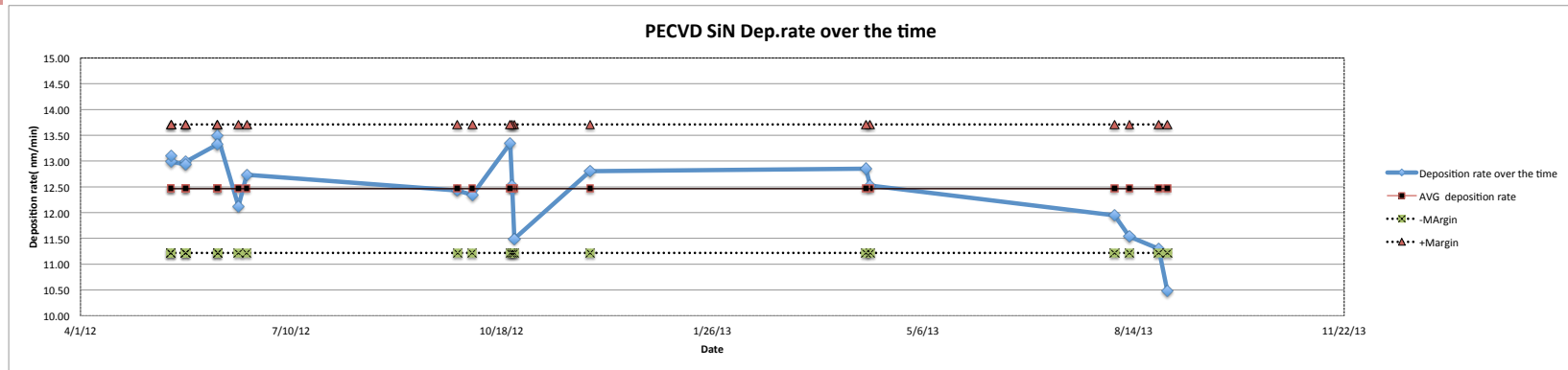


Date	User	Material	Recipe	Substrate temperature	Measured Thickness	Dep.time (min,sec)	Dep.time (sec)	Refractive index @JAW		AVG index @632.8nm	AVG index +5%	AVG index -5%	Dep.rate	Stress	HF etch rate	AFM		LPD (light point defects)		AVG dep.rate	AVG d.r.+10%	AVG d.r.-10%	Additional Notes
								EC-400 Woolam Spectroscopic	1550nm							Ra	Rmax	before dep.	after dep.				
1/1/2012	User	SIN	SIN_10	250 C	550 (A)	3min 20sec		1.98	1.961				124 (A/min)	Tensile(+456MPa)	(nm/min)	nm	nm	before dep.	after dep.				
8/30/13	Biljana	SIN	SIN_10	250	858.34	8'11.2"	491.2	1.941	1.890	1.959	2.056	1.861	10.48	532.57	71.20*			43	711	12.46	13.71	11.22	Small pieces(1/2X1/2) inch**
8/28/13	Biljana	SIN	SIN_10	250	924.82	8'11.2"	491.2	1.926	1.877	1.959	2.056	1.861	11.30					4974	10353(fail)	12.46	13.71	11.22	4" Si wafer(Intensity bellow check limit!)
8/12/13	Biljana	SIN	SIN_14	250	1322.06	11'27.7"	687.7	1.934	1.888	1.959	2.056	1.861	11.53							12.46	13.71	11.22	4" Si wafer(Intensity bellow check limit!)
8/5/13	Biljana	SIN	SIN_18	250	1761.00	14'44.2"	884.2	1.890		1.959	2.056	1.861	11.95							12.46	13.71	11.22	1/4" InP quarter
4/11/13	Biljana	SIN	SIN_10	250	1025.47	8'11.2"	491.2	1.972	1.920	1.959	2.056	1.861	12.53							12.46	13.71	11.22	2" Si wafer (wafer thickness~280um)
4/9/13	Biljana	SIN	SIN_10	250	1052.00	8'11.2"	491.2	1.964		1.959	2.056	1.861	12.85							12.46	13.71	11.22	2" InP wafer (wafer thickness=366um)
11/29/12	Omar	SIN	SIN_30	250	1048.33	8'11.2"	491.2	1.987	1.917	1.959	2.056	1.861	12.81	417.87		0.156	1.85			12.46	13.71	11.22	4" wafer
10/24/12	Biljana	SIN**	SIN_30	250	2823.01	24'33.6"	1473.6	1.994	1.960	1.959	2.056	1.861	11.49	not done	51.77**			no	no	12.46	13.71	11.22	Small pieces(1/2X1/2) inch**
10/23/12	Biljana	SIN	SIN_10	250	1025.75	8'11.2"	491.2	1.973	1.918	1.959	2.056	1.861	12.53	355.01*				558	864	12.46	13.71	11.22	4" Si wafer
10/22/12	Biljana	SIN	SIN_10	250	1092.65	8'11.2"	491.2	1.967	1.920	1.959	2.056	1.861	13.35	not done				no	no	12.46	13.71	11.22	4" Si wafer
10/4/12	Biljana	SIN	SIN_10	250	2021.21	16'22.4"	982.4	1.966	1.917	1.959	2.056	1.861	12.34	321.19				21	56	12.46	13.71	11.22	4" Si wafer
9/27/12	Biljana	SIN	SIN_10	250	1017.37	8'11.2"	491.2	1.961	1.911	1.959	2.056	1.861	12.43	467.38	65.34			56	104	12.46	13.71	11.22	4" Si wafer, HF etch rate (quarters)
6/19/12	Biljana	SIN	SIN_10	250	1042.52	8'11.2"	491.2	1.964		1.959	2.056	1.861	12.73					234	348	12.46	13.71	11.22	4" Si wafer
6/15/12	Biljana	SIN	SIN_30	250	2977.50	24'33.6"	1473.6	1.962		1.959	2.056	1.861	12.12					164	4868	12.46	13.71	11.22	4" Si wafer
6/5/12	Biljana	SIN	SIN_10	250	1105.12	8'11.2"	491.2	1.969		1.959	2.056	1.861	13.50					419	501	12.46	13.71	11.22	4" Si wafer
6/5/12	Biljana	SIN	SIN_10	250	1090.90	8'11.2"	491.2	1.967		1.959	2.056	1.861	13.33					656	698	12.46	13.71	11.22	4" Si wafer
5/21/12	Biljana	SIN	SIN_10	250	1063.03	8'11.2"	491.2	1.960		1.959	2.056	1.861	12.98					123	184	12.46	13.71	11.22	4" Si wafer
5/21/12	Biljana	SIN	SIN_10	250	1059.30	8'11.2"	491.2	1.959		1.959	2.056	1.861	12.94					85	144	12.46	13.71	11.22	4" Si wafer
5/14/12	Biljana	SIN	SIN_30	250	3189.83	24'33.6"	1473.6	1.954		1.959	2.056	1.861	12.99					315	2843	12.46	13.71	11.22	4" Si wafer
5/14/12	Biljana	SIN	SIN_10	250	1072.30	8'11.2"	491.2	1.961		1.959	2.056	1.861	13.10					224	283	12.46	13.71	11.22	4" Si wafer

* Ning, 2000A, stress=260MPa
 * Ning, 2000A, HF e.r.=36nm/min

*Bilja, 1000A, stress~+350MPa
 **Bilja, 3000A, HF e.r.=52nm/min
 Avg Dep.Rate 12.46
 Avg +10% 13.71
 Avg -10% 11.22

SIN uniform HF etch!



Avg Index 1.959
Avg +5% 2.056
Avg - 5% 1.861

